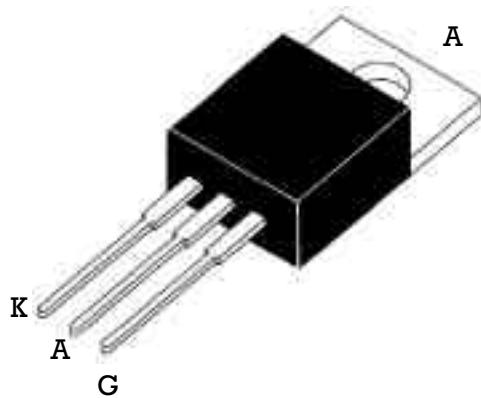


## SENSITIVE GATE SCR

<b>TO220-AB</b> 	<b>On-State Current</b> 4 Amp	<b>Gate Trigger Current</b> < 200 $\mu$ A
	<b>Off-State Voltage</b> 200 V ÷ 600 V	
<p>These series of <b>Silicon Controlled Rectifier</b> use a high performance PNPN technology.</p> <p>These parts are intended for general purpose applications where high gate sensitivity is required.</p>		

### Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Min.	Max.	Unit
$I_{T(RMS)}$	On-state Current	180° Conduction Angle, $T_c = 115^\circ C$		4	A
$I_{T(AV)}$	Average On-state Current	Half Cycle, $\alpha = 180^\circ$ , $T_c = 115^\circ C$		2.5	A
$I_{TSM}$	Non-repetitive On-State Current	Half Cycle, 60 Hz		33	A
$I_{TSM}$	Non-repetitive On-State Current	Half Cycle, 50 Hz		30	A
$I^{2t}$	Fusing Current	$t_p = 10ms$ , Half Cycle		4.5	$A^2s$
$V_{GRM}$	Peak Reverse Gate Voltage	$I_{GR} = 10 \mu A$		8	V
$I_{GM}$	Peak Gate Current	20 $\mu s$ max.		4	A
$P_{GM}$	Peak Gate Dissipation	20 $\mu s$ max.		5	W
$P_{G(AV)}$	Gate Dissipation	20ms max.		0.5	W
$T_j$	Operating Temperature		-40	+125	$^\circ C$
$T_{stg}$	Storage Temperature		-40	+150	$^\circ C$
$T_{sld}$	Soldering Temperature	10s max.		260	$^\circ C$

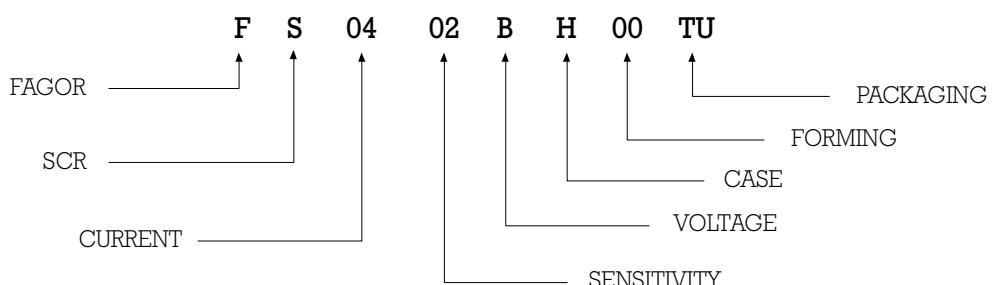
SYMBOL	PARAMETER	CONDITIONS	VOLTAGE			Unit
			B	D	M	
$V_{DRM}$ $V_{RRM}$	Repetitive Peak Off State Voltage	$R_{GK} = 1 K$	200	400	600	V

## SENSITIVE GATE SCR

## Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	SENSITIVITY		Unit
			02		
$I_{GT}$	Gate Trigger Current	$V_D = 12 \text{ V}_{DC}, R_L = 33 \Omega, T_j = 25^\circ\text{C}$	MAX	200	$\mu\text{A}$
$I_{DRM} / I_{RRM}$	Off-State Leakage Current	$V_D = V_{DRM}, R_{GK} = 220 \Omega, T_j = 125^\circ\text{C}$ $V_R = V_{RRM}, T_j = 25^\circ\text{C}$	MAX MAX	1 5	$\text{mA}$ $\mu\text{A}$
$V_{TM}$	On-state Voltage	at $I_T = 8 \text{ Amp}, t_p = 380 \mu\text{s}, T_j = 25^\circ\text{C}$	MAX	1.6	V
$V_{GT}$	Gate Trigger Voltage	$V_D = 12 \text{ V}_{DC}, R_L = 33 \Omega, T_j = 25^\circ\text{C}$	MAX	0.8	V
$V_{GD}$	Gate Non Trigger Voltage	$V_D = V_{DRM}, R_L = 3.3\text{K}, R_{GK} = 220 \Omega, T_j = 125^\circ\text{C}$	MIN	0.1	V
$I_H$	Holding Current	$I_T = 50 \text{ mA}, R_{GK} = 220 \Omega, T_j = 25^\circ\text{C}$	MAX	5	$\text{mA}$
$I_L$	Latching Current	$I_G = 1 \text{ mA}, R_{GK} = 1 \text{ K}$	MAX	6	$\text{mA}$
$dv/dt$	Critical Rate of Voltage Rise	$V_D = 0.65 \times V_{DRM}, R_{GK} = 220 \Omega, T_j = 125^\circ\text{C}$	MIN	5	$\text{V}/\mu\text{s}$
$di/dt$	Critical Rate of Current Rise	$I_G = 2 \times I_{GT}, t_r = 100 \text{ ns}, f = 60 \text{ Hz}, T_j = 125^\circ\text{C}$	MIN	50	$\text{A}/\mu\text{s}$
$R_{th(j-c)}$	Thermal Resistance Junction-Case for DC			3	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	Thermal Resistance Junction-Amb for DC			60	$^\circ\text{C}/\text{W}$
$V_{t0}$	Threshold Voltage	$T_j = 125^\circ\text{C}$	MAX	0.85	V
$R_d$	Dynamic resistance	$T_j = 125^\circ\text{C}$	MAX	90	m

## PART NUMBER INFORMATION



## SENSITIVE GATE SCR

Fig. 1: Maximum average power dissipation versus average on-state current.

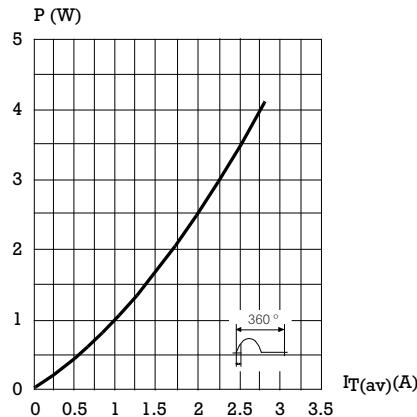


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

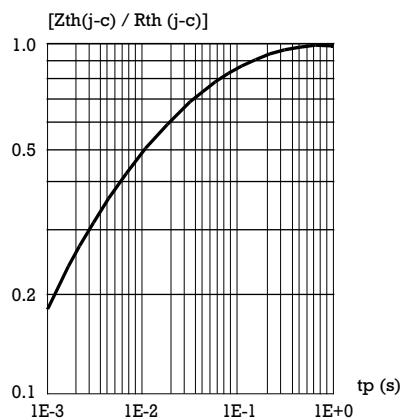


Fig. 5: Non repetitive surge peak on-state current versus number of cycles.

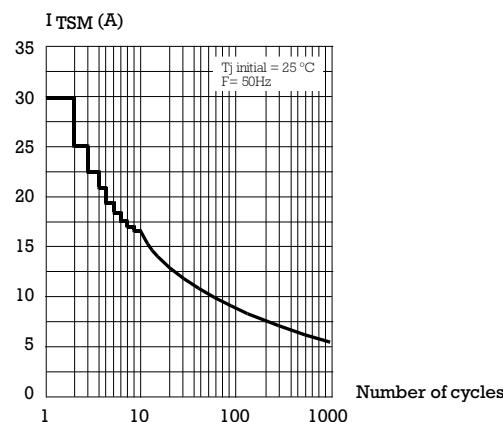


Fig. 2: Average and D.C. on-state current versus case temperature.

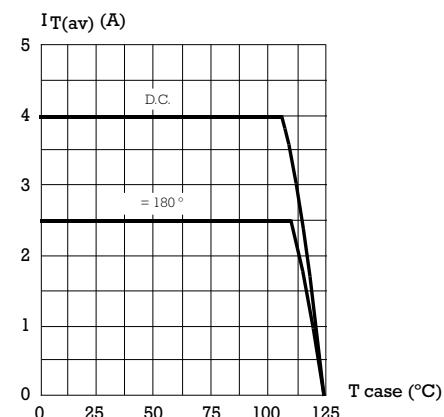


Fig. 4: Relative variation of gate trigger current, holding and latching current versus junction temperature.

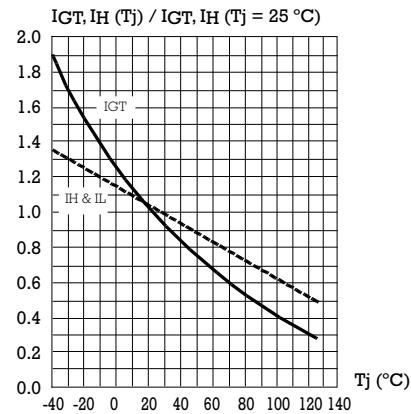
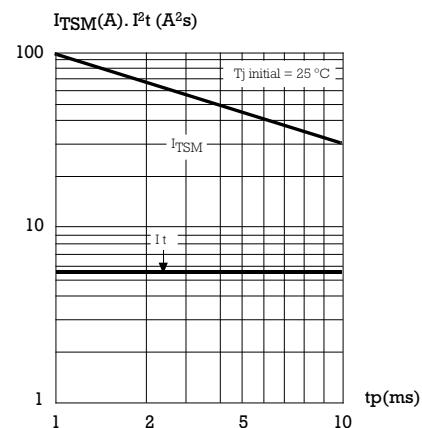
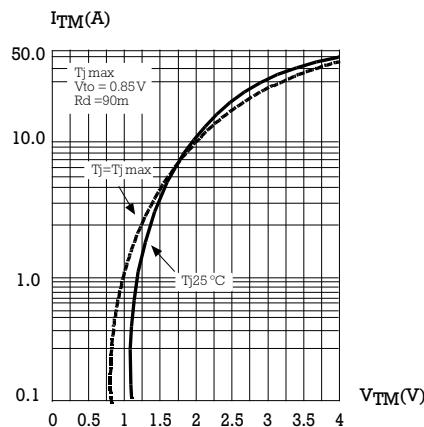


Fig. 6: Non repetitive surge peak on-state current for a sinusoidal pulse with width:  $tp < 10$  ms, and corresponding value of  $I^2t$ .



**SENSITIVE GATE SCR**

Fig. 7: On-state characteristics (maximum values).



**PACKAGE MECHANICAL DATA**

TO-220AB

Mechanical drawing of the TO-220AB package showing dimensions A through M. The drawing shows top and side views with various dimensions labeled: A, B, L, al, a1, a2, a3, b1, b2, c, cl, c2, e, F, I, I2, I3, I4, M, and 14.

REF.	DIMENSIONS		
	Milimeters		
	Min.	Nominal	Max.
A	15.20		15.90
a1		3.75	
a2	13.00		14.00
B	10.00		10.40
b1	0.61		0.88
b2	1.23		1.32
C	4.40		4.60
cl	0.49		0.70
c2	2.40		2.72
e	2.40		2.70
F	6.20		6.60
I	3.75		3.85
I4	15.80	16.40	16.80
L	2.65		2.95
I2	1.14		1.70
I3	1.14		1.70
M		2.60	